

TOSHIBA Diode Silicon Epitaxial Schottky Barrier Type

1SS396

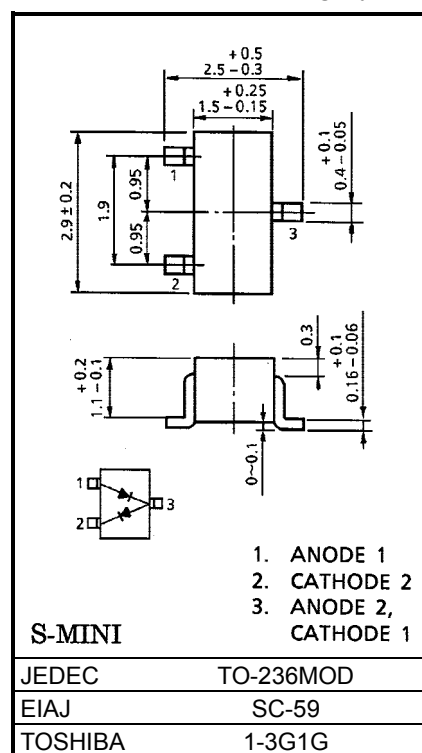
Low Voltage High Speed Switching

Unit: mm

- Low forward voltage : $V_F(3) = 0.54V$ (typ.)
- Low reverse current : $I_R = 5\mu A$ (max.)
- Small package : SC-59

Maximum Ratings ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse Voltage	V_{RM}	45	V
Reverse voltage	V_R	40	V
Maximum (peak) forward current	I_{FM}	300 *	mA
Average forward current	I_O	100 *	mA
Surge current (10ms)	I_{FSM}	1 *	A
Power dissipation	P	150	mW
Junction temperature	T_j	125	$^\circ C$
Storage temperature range	T_{stg}	-55~125	$^\circ C$
Operating temperature range	T_{opr}	-40~100	$^\circ C$

* Unit rating. Total rating = unit rating $\times$ 0.7

Weight: 0.012g

Electrical Characteristics ($T_a = 25^\circ C$)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_F(1)$	—	$I_F = 1mA$	—	0.28	—	V
	$V_F(2)$	—	$I_F = 10mA$	—	0.36	—	
	$V_F(3)$	—	$I_F = 100mA$	—	0.54	0.60	
Reverse current	I_R	—	$V_R = 40V$	—	—	5	μA
Total capacitance	C_T	—	$V_R = 0, f = 1MHz$	—	18	25	pF

Marking

